

2SC1214

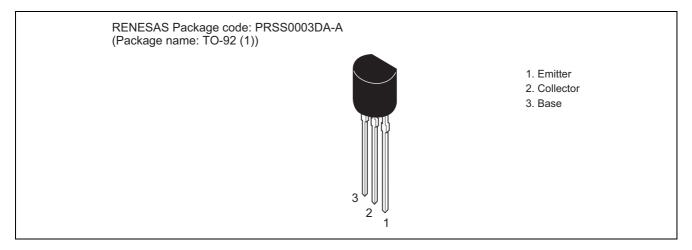
Silicon NPN Epitaxial

REJ03G0686-0200 (Previous ADE-208-1050) Rev.2.00 Aug.10.2005

Application

Low frequency amplifier

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit	
Collector to base voltage	V_{CBO}	50	V	
Collector to emitter voltage	V_{CEO}	50	V	
Emitter to base voltage	V_{EBO}	4	V	
Collector current	Ic	500	mA	
Collector power dissipation	Pc	600	mW	
Junction temperature	Tj	150	°C	
Storage temperature	Tstg	-55 to +150	°C	

Electrical Characteristics

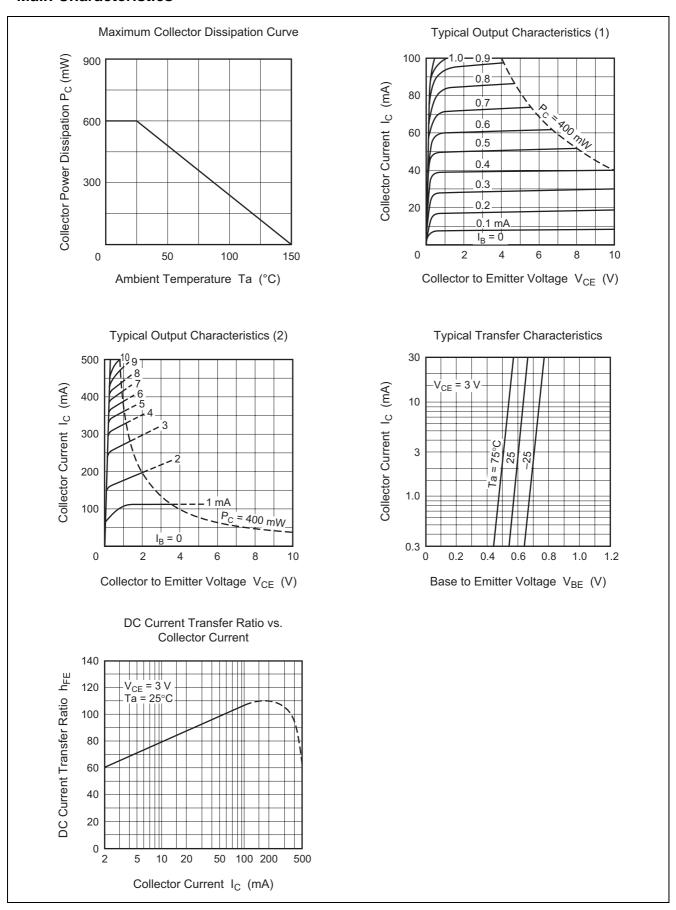
 $(Ta = 25^{\circ}C)$

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	50	_	_	V	$I_C = 10 \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	50	_	_	V	$I_C = 1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	4	_	_	V	$I_E = 10 \mu A, I_C = 0$
Collector cutoff current	I _{CBO}	_	_	0.5	μΑ	$V_{CB} = 20 \text{ V}, I_E = 0$
DC current transfer ratio	$h_{FE}^{*^1}$	60	_	320		$V_{CE} = 3 \text{ V}, I_{C} = 10 \text{ mA}$
	h _{FE}	10	_	_		$V_{CE} = 3 \text{ V, } I_{C} = 500 \text{ mA}$ (pulse test)
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	0.2	0.6		$I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$ (Pulse test)
Base to emitter voltage	V_{BE}	_	0.64	_	V	$V_{CE} = 3 \text{ V}, I_{C} = 10 \text{ mA}$

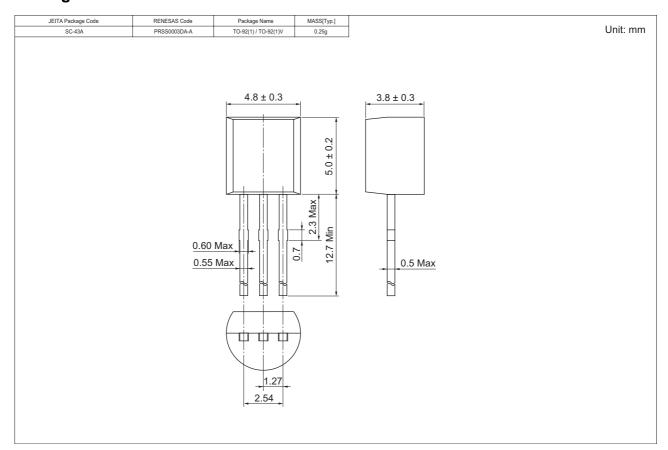
Note: 1. The 2SC1214 is grouped by h_{FE} as follows.

В	С	D	
60 to 120	100 to 200	160 to 320	

Main Characteristics



Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container		
2SC1214CTZ-E	2500	Hold Box, Radial Taping		
2SC1214DTZ-E				

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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